



## INFORMATIONDISCLOSURECITATION

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12318-US									

Application Number 10/021,081

Applicant(s)

		(Use several sheets if neces	sary)		Dan-xia Xu et al.				
					Filing Date Group Art Unit December 19, 2001 2878				
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INFORMATIONDISCLOSURECITATION

Application Number Docket Number (Optional) 10/021,081 12318-US

Applicant(s) Dan-xia Xu et al.

## (Use several sheets if necessary) Group Art Unit Filing Date 2878 December 19, 2001 U.S. PATENT DOCUMENTS **FILING DATE** SUBCLASS CLASS NAME EXAMINER DOCUMENT NUMBER DATE IF APPROPRIATE INITIAL FOREIGN PATENT DOCUMENTS Translation CLASS SUBCLASS COUNTRY DATE DOCUMENT NUMBER YES NO OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) "Si/SiO resonant cavity photodetector", D. C. Diaz et al., American Institute of Physics, Appl. Phys. Lett. 69 (19), November 4, 1996, pages 2798-2800. "Fabrication of ultrafast Si based MSM photodetector", M. Loken et al., Electronics Letters, Vol. 34, No. 10, May 14, 1998. Pages 1027-1028. "A Vertical Cavity Longwave Infrared SiGe/Si Photodetector Using a Buried Silicide Mirror", R.T. Carline et al., Defence Evaluation and Research Agency, Pages 36.1.1-36.1.4. "Selective Epitaxial Growth Si Resonant-Cavity Photodetector", IEEE Photonics Technology Letters, Vol. 10, No. 1, January 1998, pages 129-131.

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## Oocket Number (Optional) Application Number 12318-US 10/021,081 INFORMATIONDISCLOSURECITATIO Applicant(s) Dan-xia Xu et al (Use several sheets if necessary) Filing Date Group Art Unit December 19, 2001 \*EXAMINER OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) INITIAL "SOI waveguide GeSi avalanche pin photodetector at 1.3 um wavelength, Tomomi Yoshimoto et al., IEICE Trans. Electron, Vol. E81, No. 10, October 10, 1998, pages 1667-1669. "High-speed metal-semiconductor-metal photodetectors fabricated on SOI-substrates, K. Honkanen et al., Physica Scripta, Vol. T79, 1999, pages 127-130. "140-GHz metal-semiconductor-metal photodetectors on silicon-on-insulator substrate with a scaled active layer", M. Y. Liu et al., Appl. Phys. Lett. 65 (7), August 15, 1994. "Comparison of the picosecond characteristics of silicon and silicon-on-sapphiremetal-semiconductor-metalphotodiodes", Chia-Chi Wang et al., Laboratory for Laser Energetics and Department of Electrical Engineering, 1994, pages 3578-3580.

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